Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

FAIRCHILD SEMICONDUCTOR™

January 2001

FDG6308P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

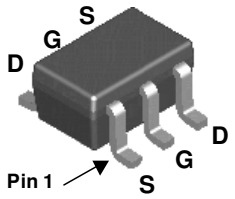
This P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

Applications

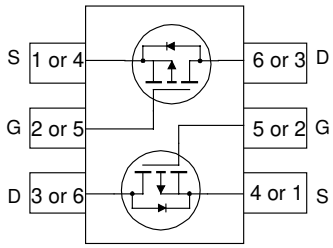
- Battery management
- Load switch

Features

- –0.6 A, –20 V. $R_{DS(ON)}$ = 0.40 Ω @ V_{GS} = –4.5 V
  $R_{DS(ON)}$ = 0.55 Ω @ V_{GS} = –2.5 V
  $R_{DS(ON)}$ = 0.80 Ω @ V_{GS} = –1.8 V
- Low gate charge
- High performance trench technology for extremely low $R_{DS(ON)}$
- Compact industry standard SC70-6 surface mount package



SC70-6



The pinouts are symmetrical; pin 1 and pin 4 are interchangeable.

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	–20	V
V_{GSS}	Gate-Source Voltage	± 8	V
I_D	Drain Current – Continuous (Note 1)	–0.6	A
	– Pulsed	–1.8	
P_D	Power Dissipation for Single Operation (Note 1)	0.3	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	415	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.08	FDG6308P	7''	8mm	3000 units

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0 V, I_D = –250 µA	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = –250 µA, Referenced to 25°C		–15		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = –16 V, V_{GS} = 0 V			–1	µA
I_{GSSF}	Gate–Body Leakage, Forward	V_{GS} = –8 V, V_{DS} = 0 V			–100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	V_{GS} = 8 V, V_{DS} = 0 V			100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = –250 µA	–0.4	–0.9	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = –250 µA, Referenced to 25°C		2		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	V_{GS} = –4.5 V, I_D = –0.6 A V_{GS} = –2.5 V, I_D = –0.5 A V_{GS} = –1.8 V, I_D = –0.4 A V_{GS} = –4.5 V, I_D = –0.6 A, T_J=125°C		0.27 0.36 0.55 0.35	0.40 0.55 0.80 0.56	Ω
$I_{D(on)}$	On–State Drain Current	V_{GS} = –4.5 V, V_{DS} = –5 V	–2			A
g_{FS}	Forward Transconductance	V_{DS} = –5 V, I_D = –0.6 A		2.1		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = –10 V, V_{GS} = 0 V, f = 1.0 MHz		153		pF
C_{oss}	Output Capacitance			25		pF
C_{rss}	Reverse Transfer Capacitance			9		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = –10 V, I_D = 1 A, V_{GS} = –4.5 V, R_{GEN} = 6 Ω		5	10	ns
t_r	Turn–On Rise Time			15	27	ns
$t_{d(off)}$	Turn–Off Delay Time			7	14	ns
t_f	Turn–Off Fall Time			1.6	3.2	ns
Q_g	Total Gate Charge	V_{DS} = –10 V, I_D = –0.6 A, V_{GS} = –4.5 V		1.8	2.5	nC
Q_{gs}	Gate–Source Charge			0.3		nC
Q_{gd}	Gate–Drain Charge			0.4		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				–0.25	A
V_{SD}	Drain–Source Diode Forward Voltage	V_{GS} = 0 V, I_S = –0.25 A (Note 2)		–0.77	–1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. $R_{\theta JA}$ = 415°C/W when mounted on a minimum pad .

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics

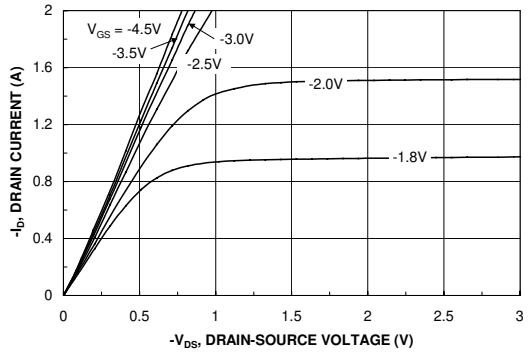


Figure 1. On-Region Characteristics.

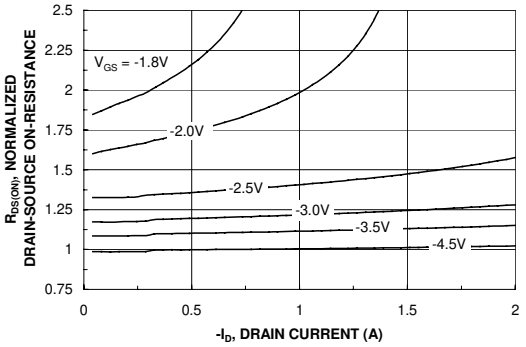


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

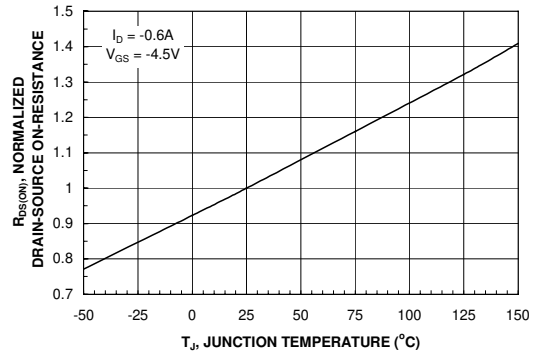


Figure 3. On-Resistance Variation with Temperature.

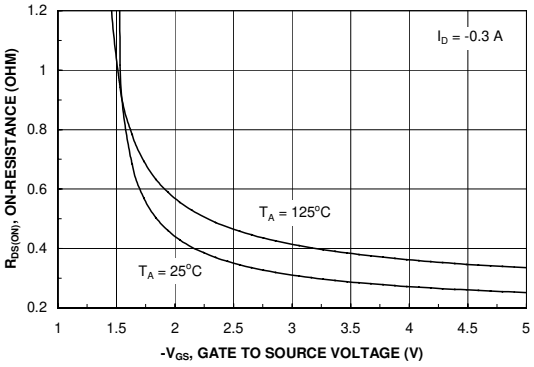


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

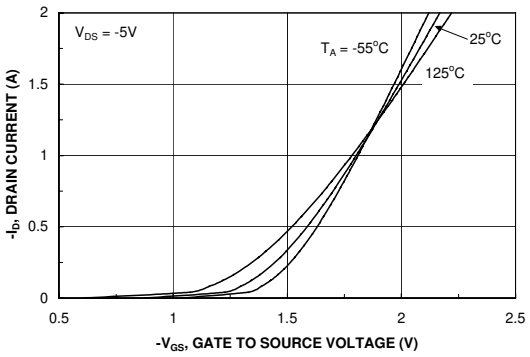


Figure 5. Transfer Characteristics.

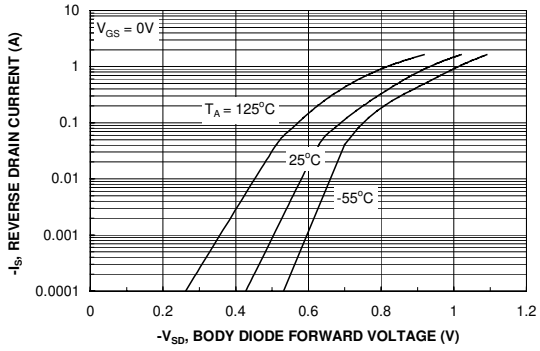


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

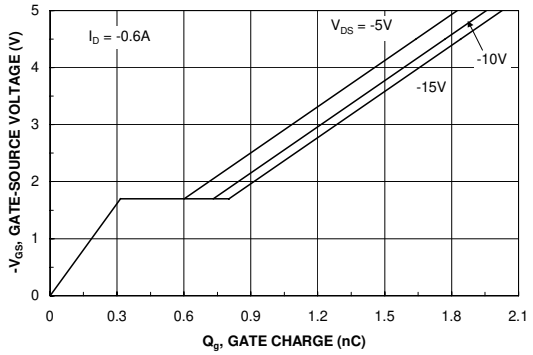


Figure 7. Gate Charge Characteristics.

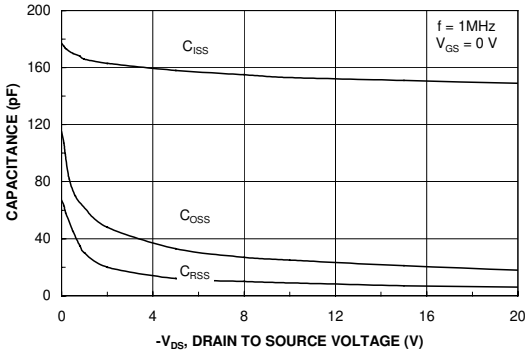


Figure 8. Capacitance Characteristics.

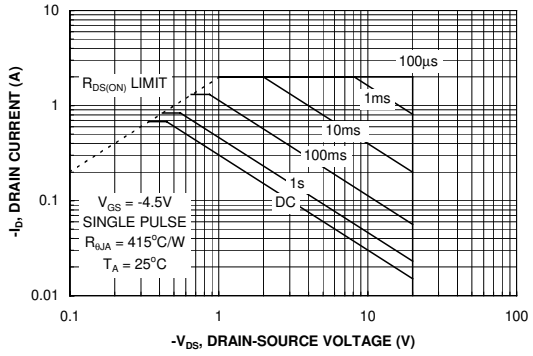


Figure 9. Maximum Safe Operating Area.

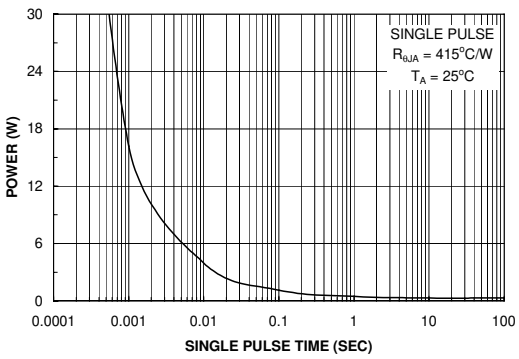


Figure 10. Single Pulse Maximum Power Dissipation.

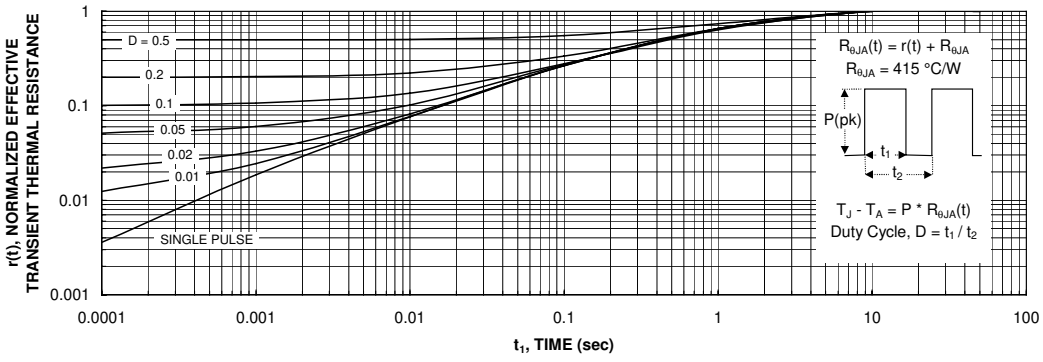


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1.
Transient thermal response will change depending on the circuit board design.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative